

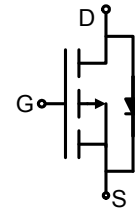
P-Channel Power MOSFET

General Features

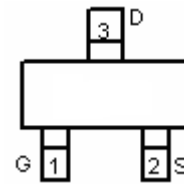
- $V_{DS} = -30V, I_D = -4A$
 $R_{DS(ON)} < 130m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 85m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and Pin Assignment



SOT-23 top view

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-4	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-18	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	78	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$	-	-	-1	μA

Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-4.0A$	-	45	60	m Ω
		$V_{GS}=-4.5V, I_D=-3.7A$	-	65	85	m Ω
		$V_{GS}=-2.5V, I_D=-2A$		100	130	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4.0A$	-	10	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	880	-	PF
Output Capacitance	C_{OSS}		-	105	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	65	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-4.0A$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	7	-	nS
Turn-on Rise Time	t_r		-	3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-4.0A, V_{GS}=-4.5V$	-	8.5	-	nC
Gate-Source Charge	Q_{gs}		-	1.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=-4.0A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics



Figure 1: Switching Test Circuit

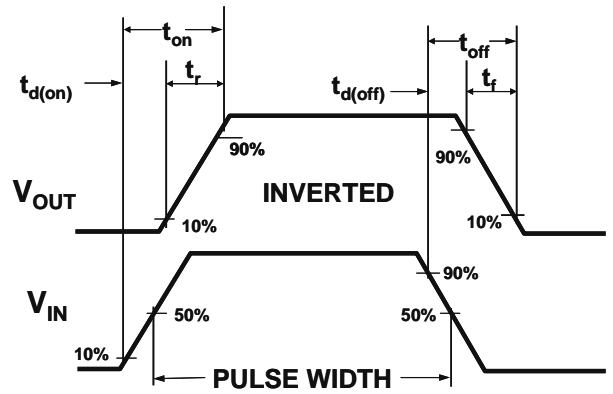
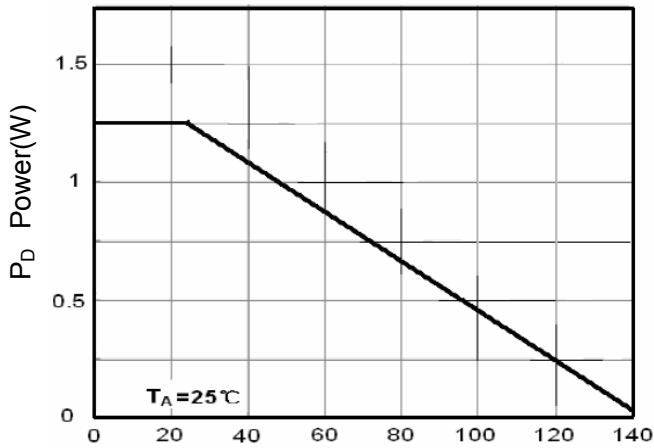
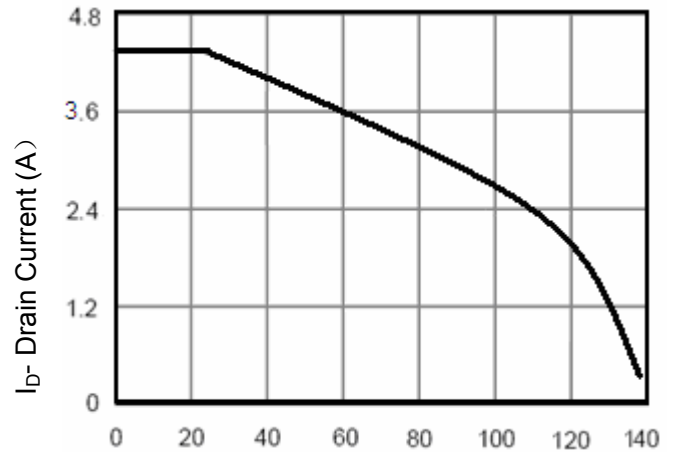


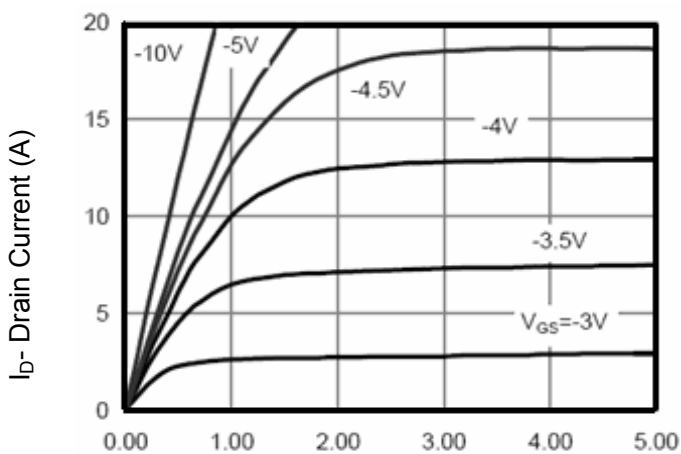
Figure 2: Switching Waveforms



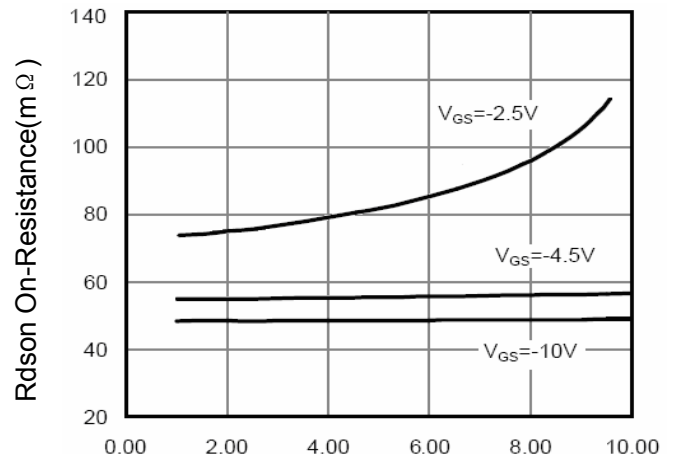
T_J-Junction Temperature(°C)
Figure 3 Power Dissipation



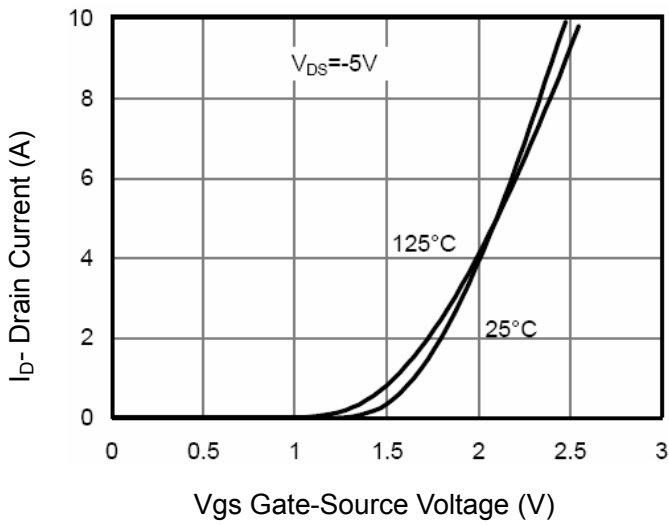
T_J-Junction Temperature(°C)
Figure 4 Drain Current



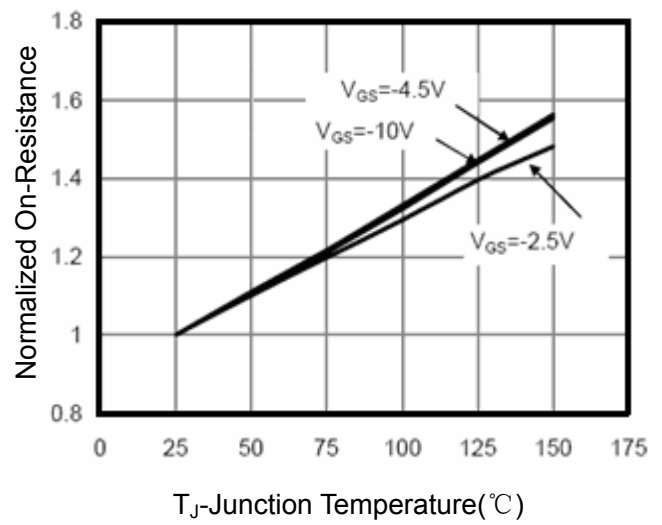
V_{ds} Drain-Source Voltage (V)
Figure 5 Output Characteristics



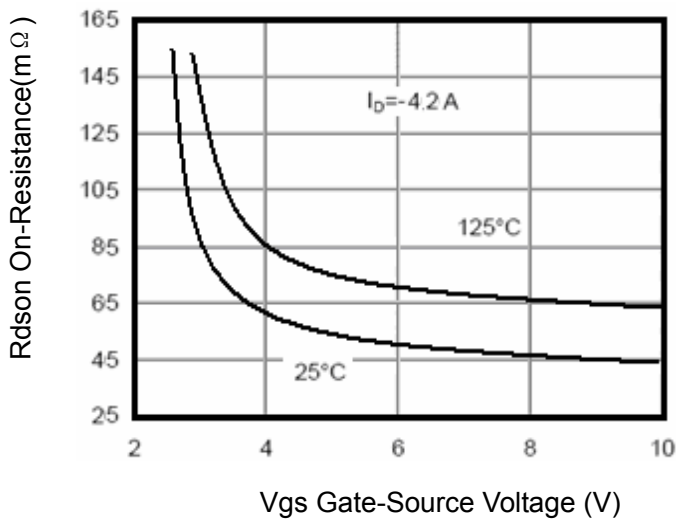
I_D- Drain Current (A)
Figure 6 Drain-Source On-Resistance



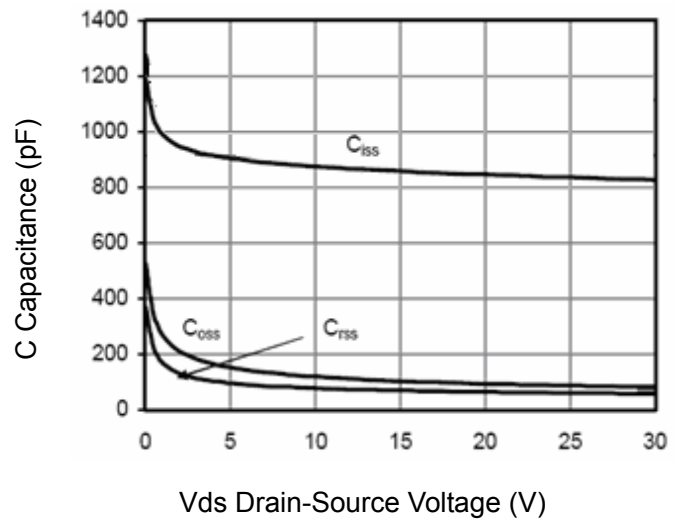
V_{gs} Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



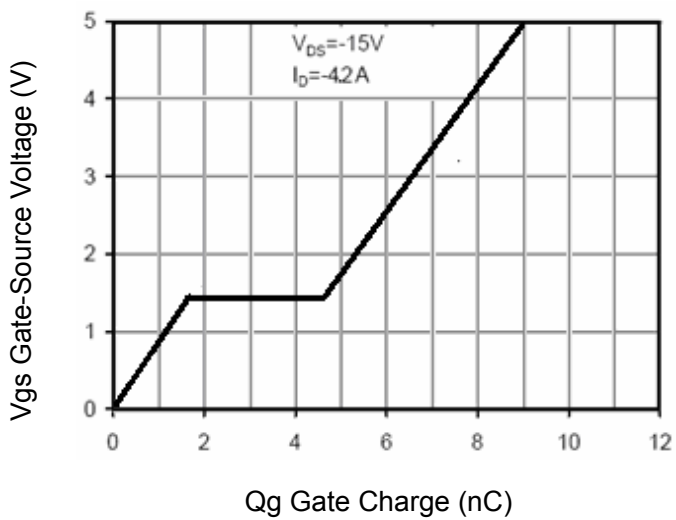
T_J-Junction Temperature(°C)
Figure 8 Drain-Source On-Resistance



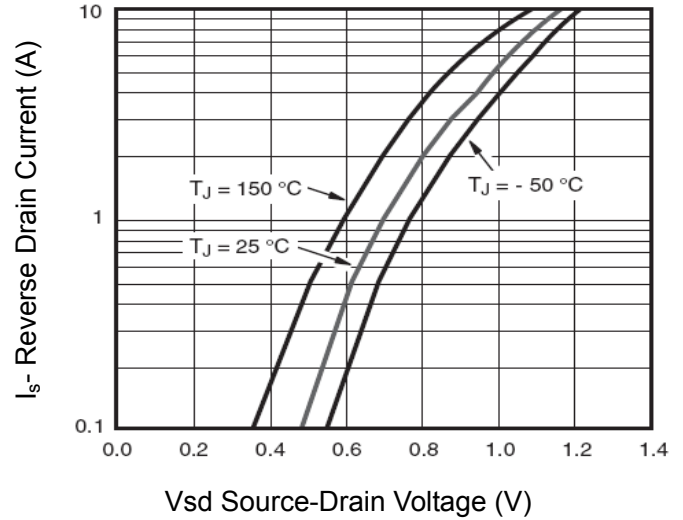
V_{gs} Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



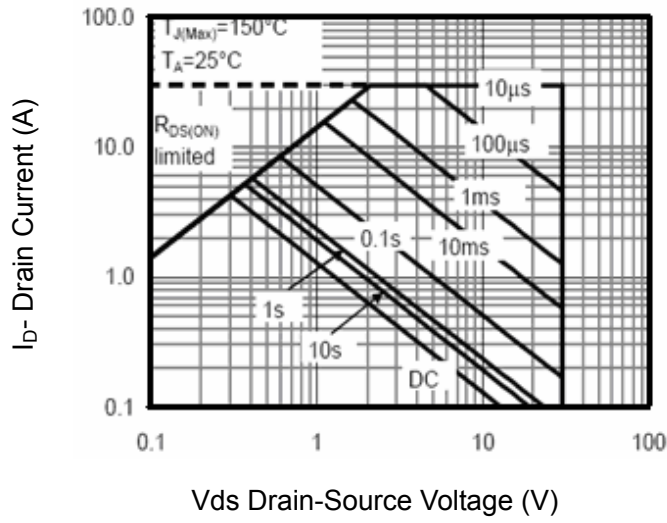
V_{ds} Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Q_g Gate Charge (nC)
Figure 11 Gate Charge



V_{sd} Source-Drain Voltage (V)
Figure 12 Source-Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

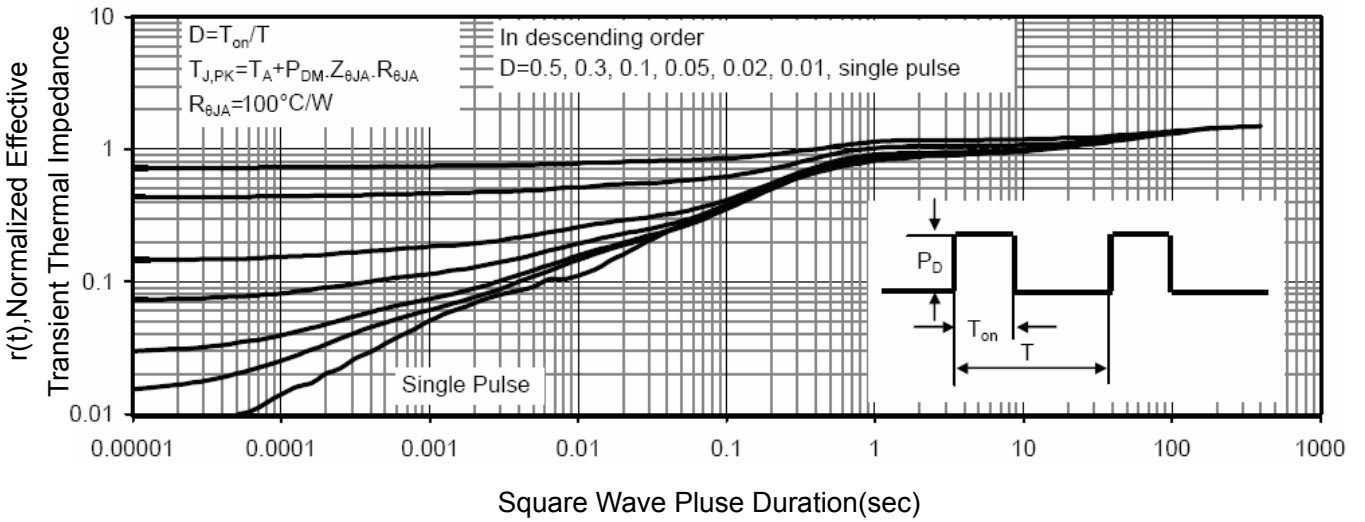
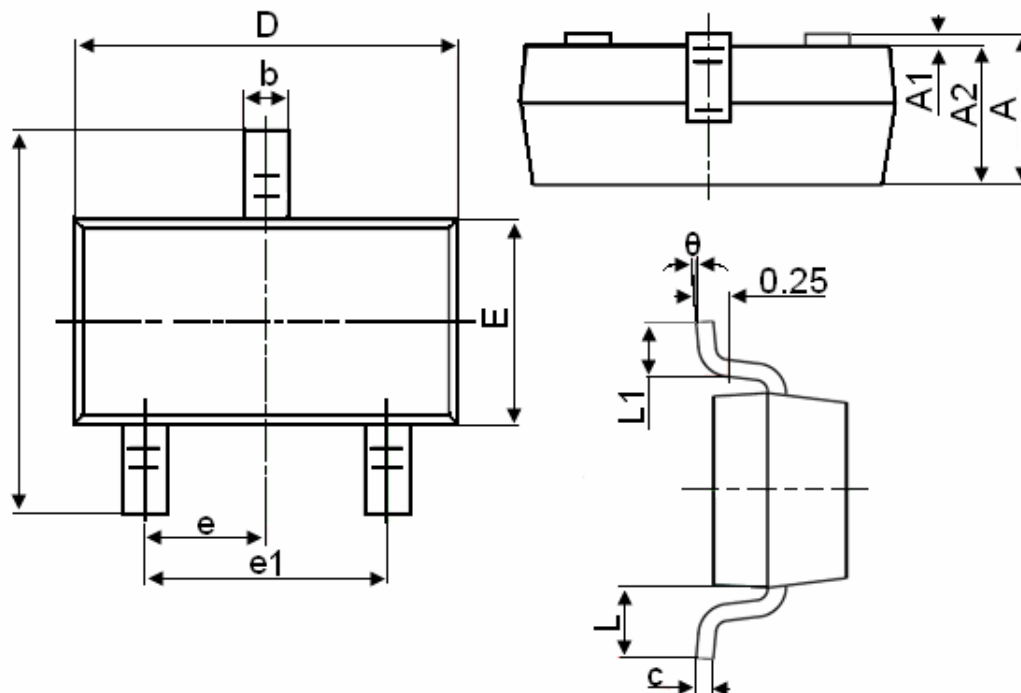


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information


Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°